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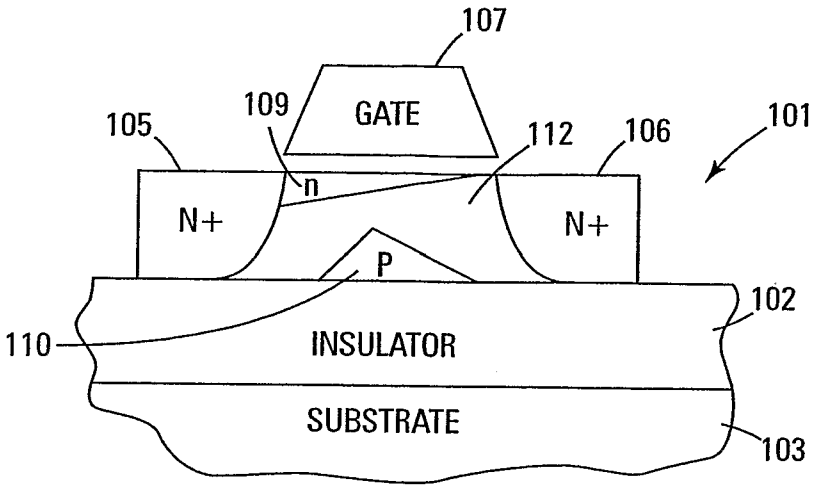
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(54) Title: FULLY DEPLETED SILICON-ON-INSULATOR CMOS LOGIC



(57) Abstract: An extractor implanted region is used in a silicon-on-insulator CMOS memory device. The extractor region is reversed biased to remove minority carriers from the body region of partially depleted memory cells. This causes the body region to be fully depleted without the adverse floating body effects.

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